

Title: TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10

Number: 5205/023

Issue: 4

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Paragraph: 2.4.1 Room Temperature Electrical Measurements

Original wording: See document an attachment.

Proposed wording: See document an attachment.

Justification: See document an attachment.

The limits defined at the initial qualification had been fixed on a qualification lot. Now that the volume of production increases and other diffusion lots are received, it is found that the limit at 6nC is too close to the distribution.

Moreover, the delta Qgd min / Qgd max is fixed by a rule (+/- 25% maximum of typ value), therefore, by increasing the Qgd max, the Qgd min must be increased.

STMicroelectronics propose the new limits for the Ggd test on the STRH8N10 product (see proposal limits the table below).

			Room Temperature Electrical Measurements	
Product	Line	ESCC	Qgd (nC) min current to New	Qgd (nC) max current to New
STRH8N10	HG0C	5205023	3.5 to 4.3	6 to 6.5